

# **UTC** UNISONIC TECHNOLOGIES CO., LTD

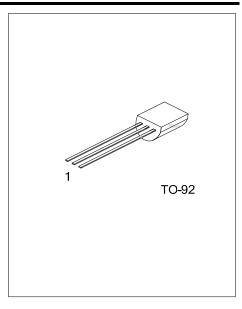
# 9015

Preliminary PNP EPITAXIAL SILICON TRANSISTOR

# **PRE-AMPLIFIER, LOW LEVEL &** LOW NOISE

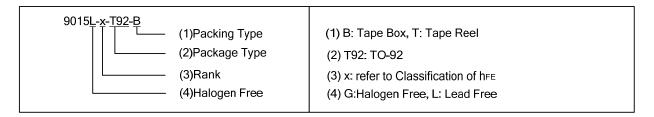
# **FEATURES**

- \* High total power dissipation. (450mW)
- \* Excellent hFE linearity.
- \* Complementary to UTC 9014



#### **ORDERING INFORMATION**

Ordering Number		Dookogo	Dooking	
Lead Free	Halogen Free	Package	Packing	
9015L-x-T92-B	9015G-x-T92-B	TO-92	Tape Box	
9015L-x-T92-K	9015G-x-T92-K	TO-92	Bulk	
9015L-x-T92-T	9015G-x-T92-T	TO-92	Tape Reel	



# Preliminary PNP EPITAXIAL SILICON TRANSISTOR

## ■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified )

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-45	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current	Ι <sub>C</sub>	-100	mA
Collector Dissipation	Pc	450	mW
Junction Temperature	TJ	+150	°C
Storage Temperature	T <sub>STG</sub>	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

### ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	$I_{\rm C} = -100 \mu {\rm A}, \ I_{\rm E} = 0$	-50			V
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	$I_{\rm C} = -1 {\rm mA},  I_{\rm B} = 0$	-45			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_{\rm E} = -100 \mu A, I_{\rm C} = 0$	-5			V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -100mA, I <sub>B</sub> = -5mA		-0.2	-0.7	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -100mA, I <sub>B</sub> = -5mA		-0.82	-1.0	V
Base-Emitter On Voltage	V <sub>BE(on)</sub>	$V_{CE} = -5V, I_{C} = -2mA$	-0.6	-0.65	-0.75	V
Collector Cutoff Current	I <sub>CBO</sub>	$V_{CB} = -50V, I_{E} = 0$			-50	nA
Emitter Cutoff Current	I <sub>EBO</sub>	$V_{EB} = -5V, I_{C} = 0$			-100	nA
DC Current Gain	h <sub>FE</sub>	$V_{CE} = -5V, I_{C} = -1mA$	60	200	600	
Output Capacitance	C <sub>ob</sub>	$V_{CB} = -10V, I_E = 0, f = 1MHz$		4.5	7.0	рF
Current Gain-Bandwidth Product	f⊤	$V_{CE} = -5V, I_{C} = -10mA$	100	190		MHz
Noise Figure	NF	V <sub>CE</sub> = -5V, I <sub>C</sub> = -0.2mA f = 1KHz, Rs = 1KΩ		0.7	10	dB

## CLASSIFICATION OF h<sub>FE</sub>

RANK	А	В	С
RANGE	60-150	100-300	200-600

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